

MOSFETs Silicon N-Channel MOS

# SSM3K16CTC

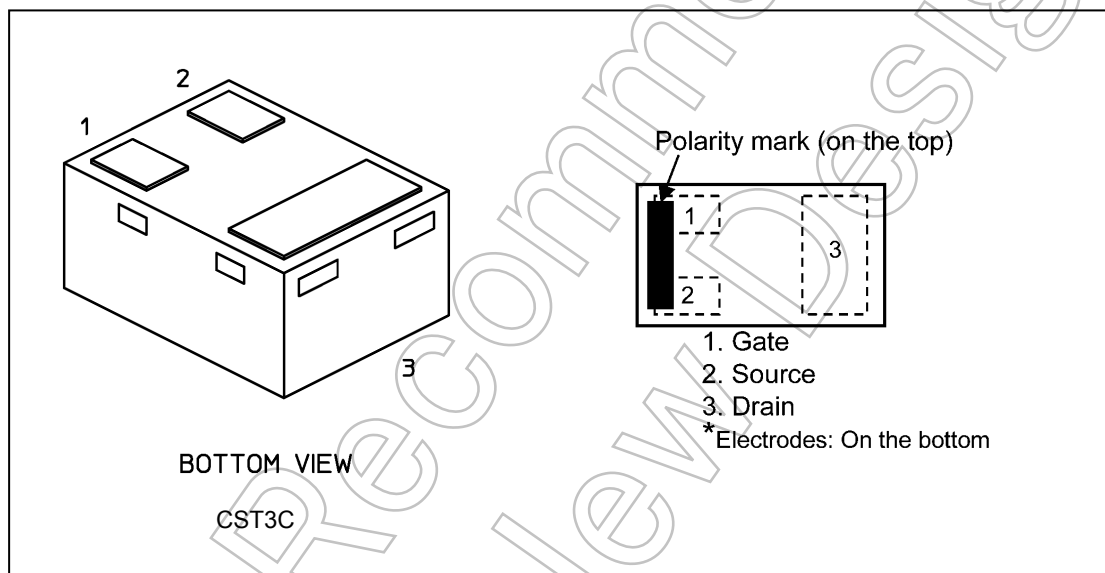
## 1. Applications

- High-Speed Switching
- Analog Switches

## 2. Features

- (1) 1.5 V gate drive voltage.
- (2) Low drain-source on-resistance  
 $R_{DS(ON)} = 5.6 \Omega$  (max) (@ $V_{GS} = 1.5$  V)  
 $R_{DS(ON)} = 4.0 \Omega$  (max) (@ $V_{GS} = 1.8$  V)  
 $R_{DS(ON)} = 3.0 \Omega$  (max) (@ $V_{GS} = 2.5$  V)  
 $R_{DS(ON)} = 2.2 \Omega$  (max) (@ $V_{GS} = 4.5$  V)

## 3. Packaging and Pin Assignment



Start of commercial production

2015-12

4. Absolute Maximum Ratings (Note) (Unless otherwise specified,  $T_a = 25\text{ }^{\circ}\text{C}$ )

| Characteristics                 | Symbol    | Rating     | Unit               |
|---------------------------------|-----------|------------|--------------------|
| Drain-source voltage            | $V_{DS}$  | 20         | V                  |
| Gate-source voltage             | $V_{GS}$  | $\pm 10$   | V                  |
| Drain current (DC) (Note 1)     | $I_D$     | 200        | mA                 |
| Drain current (pulsed) (Note 1) | $I_{DP}$  | 400        |                    |
| Power dissipation (Note 2)      | $P_D$     | 500        | mW                 |
| Channel temperature             | $T_{ch}$  | 150        | $^{\circ}\text{C}$ |
| Storage temperature             | $T_{stg}$ | -55 to 150 | $^{\circ}\text{C}$ |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Ensure that the channel temperature does not exceed  $150\text{ }^{\circ}\text{C}$ .

Note 2: Device mounted on a  $25.4\text{ mm} \times 25.4\text{ mm} \times 1.6\text{ mm}$  FR4 glass epoxy board (Cu pad:  $645\text{ mm}^2$ )

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

## 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$ )

| Characteristics                         | Symbol        | Test Condition                                     | Min  | Typ. | Max     | Unit          |
|---|---------------|--|------|------|---------|---------------|
| Gate leakage current                    | $I_{GSS}$     | $V_{GS} = \pm 10\text{ V}$ , $V_{DS} = 0\text{ V}$ | —    | —    | $\pm 1$ | $\mu\text{A}$ |
| Drain cut-off current                   | $I_{DSS}$     | $V_{DS} = 20\text{ V}$ , $V_{GS} = 0\text{ V}$     | —    | —    | 1       | $\mu\text{A}$ |
| Drain-source breakdown voltage          | $V_{(BR)DSS}$ | $I_D = 1\text{ mA}$ , $V_{GS} = 0\text{ V}$        | 20   | —    | —       | V             |
| Drain-source breakdown voltage (Note 1) | $V_{(BR)DSX}$ | $I_D = 1\text{ mA}$ , $V_{GS} = -10\text{ V}$      | 12   | —    | —       | V             |
| Gate threshold voltage (Note 2)         | $V_{th}$      | $V_{DS} = 3\text{ V}$ , $I_D = 1\text{ mA}$        | 0.35 | —    | 1.0     | V             |
| Drain-source on-resistance (Note 3)     | $R_{DS(ON)}$  | $I_D = 100\text{ mA}$ , $V_{GS} = 4.5\text{ V}$    | —    | 1.6  | 2.2     | $\Omega$      |
|   |               | $I_D = 50\text{ mA}$ , $V_{GS} = 2.5\text{ V}$     | —    | 2.1  | 3.0     |               |
|   |               | $I_D = 20\text{ mA}$ , $V_{GS} = 1.8\text{ V}$     | —    | 2.6  | 4.0     |               |
|   |               | $I_D = 10\text{ mA}$ , $V_{GS} = 1.5\text{ V}$     | —    | 3.0  | 5.6     |               |
| Forward transfer admittance (Note 3)    | $ Y_{fs} $    | $V_{DS} = 3\text{ V}$ , $I_D = 100\text{ mA}$      | 0.14 | 0.28 | —       | S             |

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

Take this into consideration when using the device.

Note 3: Pulse measurement.

### 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$ )

| Characteristics                | Symbol    | Test Condition  | Min | Typ. | Max | Unit |
|--------------------------------|-----------|---|-----|------|-----|------|
| Input capacitance              | $C_{iss}$ | $V_{DS} = 10\text{ V}$ , $V_{GS} = 0\text{ V}$ ,<br>$f = 1\text{ MHz}$  | —   | 12   | —   | pF   |
| Reverse transfer capacitance   | $C_{rss}$ |   | —   | 4.1  | —   |      |
| Output capacitance             | $C_{oss}$ |   | —   | 5.5  | —   |      |
| Switching time (turn-on time)  | $t_{on}$  | $V_{DD} = 10\text{ V}$ , $I_D = 100\text{ mA}$<br>$V_{GS} = 0\text{ to }2.5\text{ V}$ , $R_G = 50\text{ }\Omega$<br>Duty $\leq 1\%$ , $V_{IN}$ : $t_r$ , $t_f < 5\text{ ns}$ ,<br>Common source, See Chapter 5.3. | —   | 18   | —   | ns   |
| Switching time (turn-off time) | $t_{off}$ |   | —   | 36   | —   |      |

### 5.3. Switching Time Test Circuit

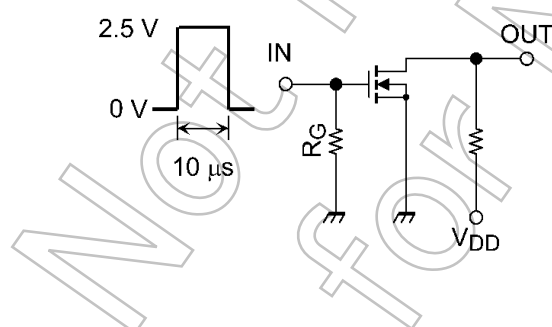


Fig. 5.3.1 Switching Time Test Circuit

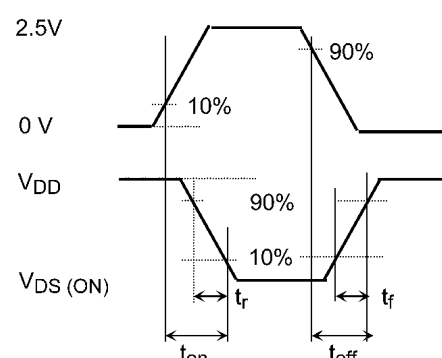


Fig. 5.3.2 Input Waveform/Output Waveform

### 5.4. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$ )

| Characteristics                | Symbol    | Test Condition                                 | Min | Typ.  | Max  | Unit |
|--------------------------------|-----------|--|-----|-------|------|------|
| Diode forward voltage (Note 1) | $V_{DSF}$ | $I_D = -200\text{ mA}$ , $V_{GS} = 0\text{ V}$ | —   | -0.89 | -1.2 | V    |

Note 1: Pulse measurement.

## 6. Marking

Polarity mark

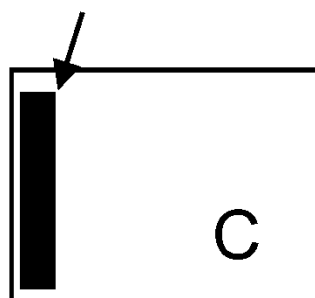
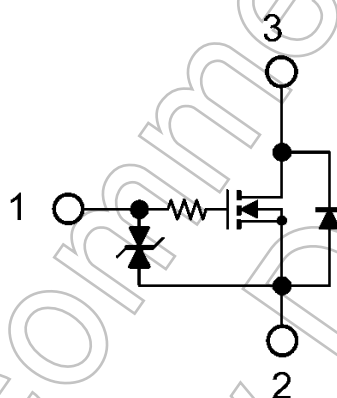


Fig. 6.1 Marking

## 7. Equivalent Circuit



## 8. Characteristics Curves (Note)

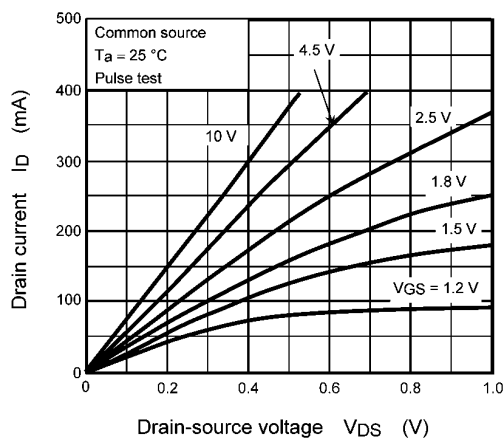


Fig. 8.1 ID - VDS

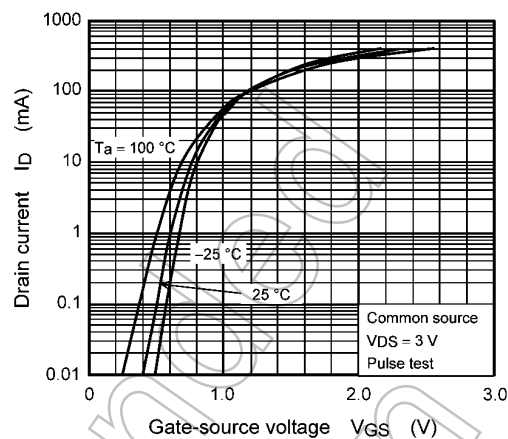


Fig. 8.2 ID - VGS

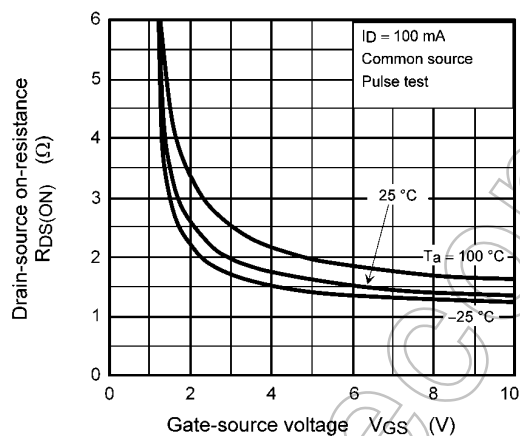


Fig. 8.3 RDS(ON) - VGS

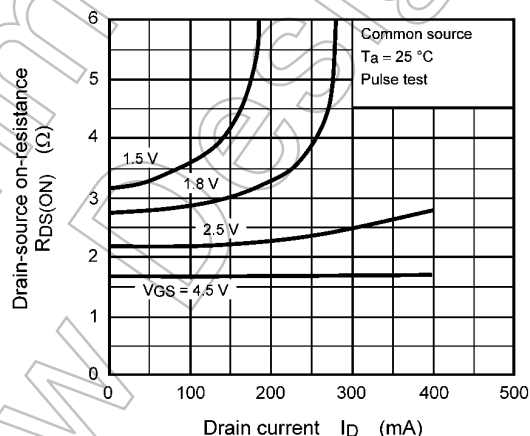


Fig. 8.4 RDS(ON) - ID

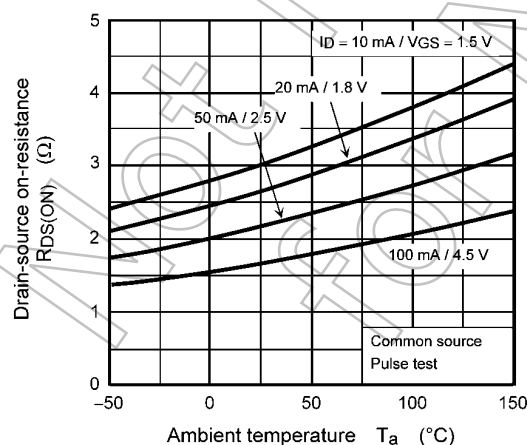


Fig. 8.5 RDS(ON) - Ta

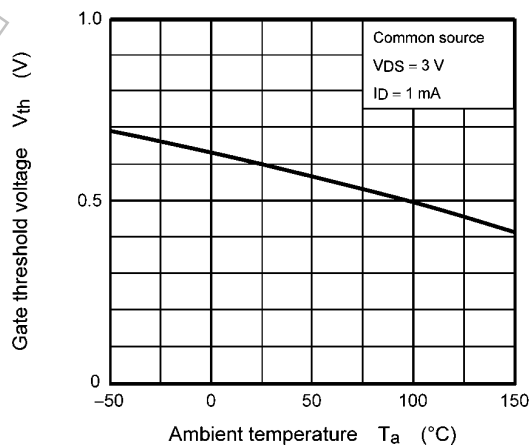


Fig. 8.6 Vth - Ta

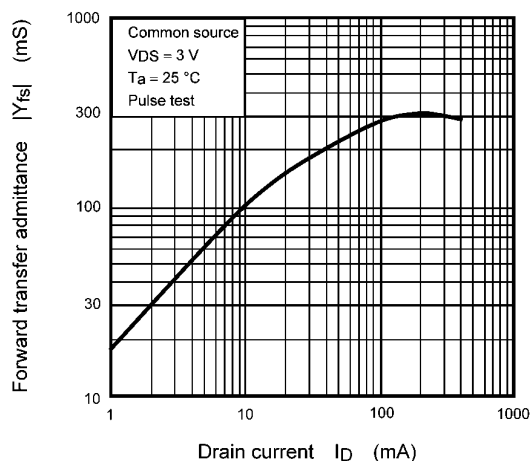


Fig. 8.7  $|Y_{fs}| - I_D$

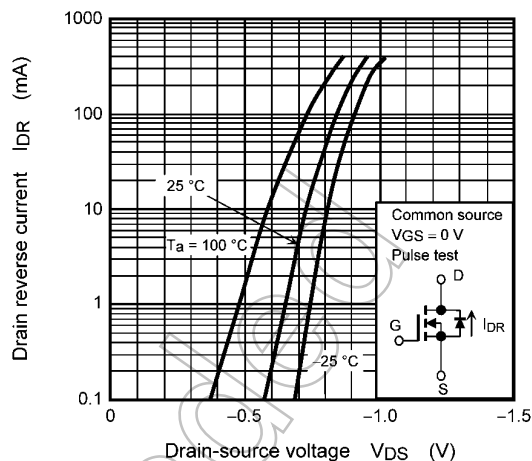


Fig. 8.8  $I_{DR} - V_{DS}$

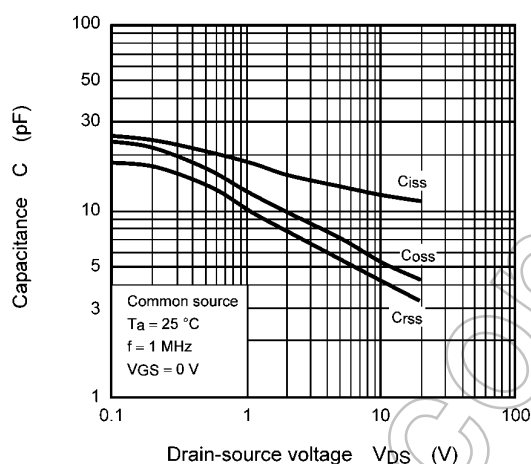


Fig. 8.9  $C - V_{DS}$

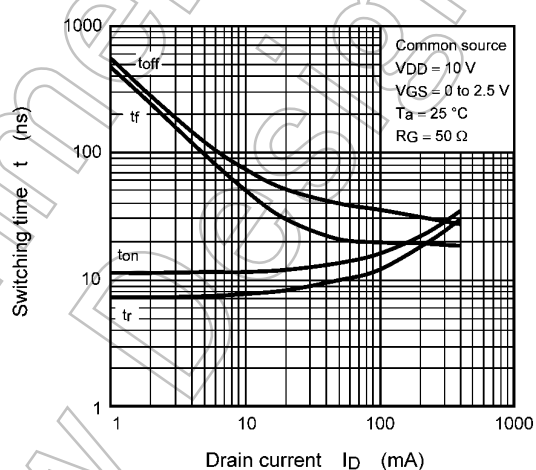


Fig. 8.10  $t - I_D$

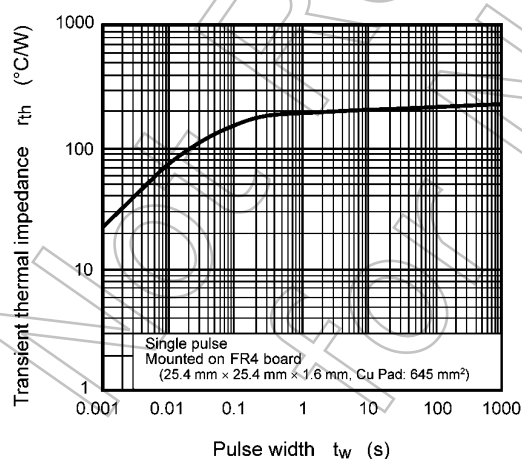


Fig. 8.11  $r_{th} - t_w$

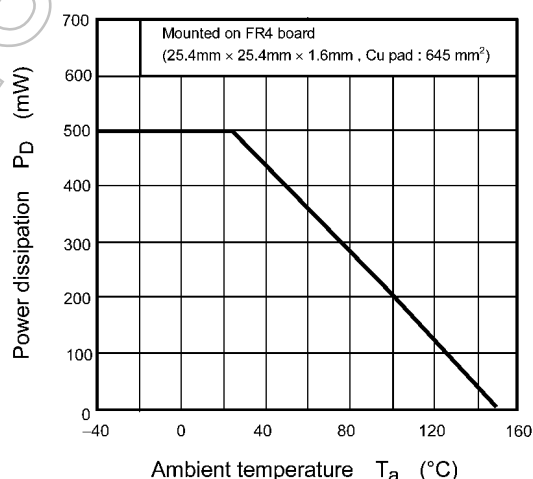
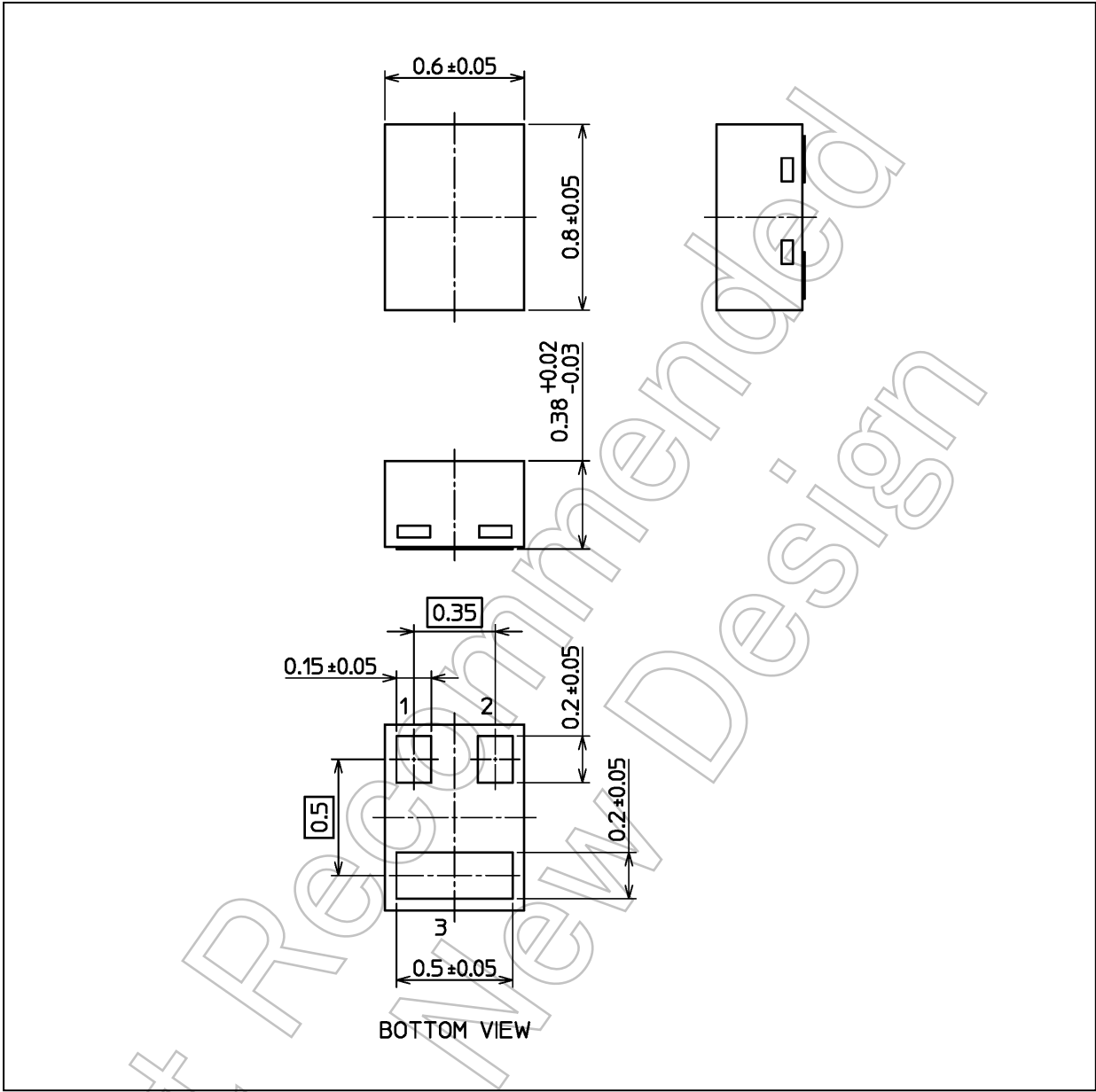


Fig. 8.12  $P_D - T_a$

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.55 mg (typ.)

| Package Name(s) |
|-----------------|
| Nickname: CST3C |

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